

INFORMATION DISCLOSURE CITATION IN AN APPLICATION				ATTY. DOCKET NO. 61352-051		SERIAL NO. 10/687,647	
(PTO-1449)				APPLICANT Yoshiaki HASEGAWA, et al.			
				FILING DATE October 20, 2003		GROUP 2811	
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EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
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EXAMINER H. P. K. K. K.				DATE CONSIDERED 12/08/04			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.